

K3473-VB Datasheet

N-Channel 900V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	900	
$R_{DS(on)}$ at 25 °C (Ω)	$V_{GS} = 10\text{ V}$	0.75
Q_g max. (nC)	20	
Q_{gs} (nC)	2.4	
Q_{gd} (nC)	11	
Configuration	Single	

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

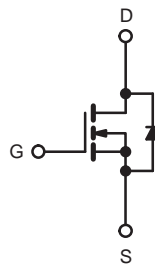
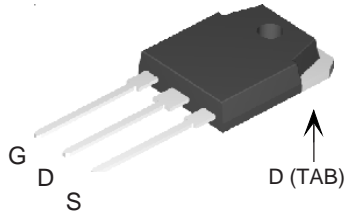


RoHS

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial

TO-3P



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	900	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	9	A
		$T_C = 100\text{ }^{\circ}\text{C}$		7.3	
Pulsed Drain Current ^a			I_{DM}	28	
Linear Derating Factor				1.89	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b			E_{AS}	86	mJ
Maximum Power Dissipation			P_D	109	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Drain-Source Voltage Slope	$T_J = 125\text{ }^{\circ}\text{C}$		dV/dt	50	V/ns
Reverse Diode dV/dt ^d		3.2			
Soldering Recommendations (Peak Temperature) ^c	for 10 s			300	$^{\circ}\text{C}$


Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ °C}$, $L = 28.2\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 3.5\text{ A}$.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100\text{ A}/\mu\text{s}$, starting $T_J = 25\text{ °C}$.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	72	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.7	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		900	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.65	-	V/ $^\circ\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 620\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$	-	0.75	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}$, $I_D = 6\text{ A}$		-	19	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$		-	373	-	pF
Output Capacitance	C_{oss}			-	26	-	
Reverse Transfer Capacitance	C_{rss}			-	14	-	
Effective Output Capacitance, Energy Related ^a	$C_{O(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}$, $V_{GS} = 0\text{ V}$		-	46	-	
Effective Output Capacitance, Time Related ^b	$C_{O(tr)}$			-	64	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$, $V_{DS} = 520\text{ V}$	-	26	-	nC
Gate-Source Charge	Q_{gs}			-	2.1	-	
Gate-Drain Charge	Q_{gd}			-	2.8	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 620\text{ V}$, $I_D = 6\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$		-	26	-	ns
Rise Time	t_r			-	55.7	-	
Turn-Off Delay Time	$t_{d(off)}$			-	71	-	
Fall Time	t_f			-	41	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain		-	3.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	7	A
Pulsed Diode Forward Current	I_{SM}			-	-	18	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 6\text{ A}$, $V_{GS} = 0\text{ V}$		-	-	1.4	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = I_S = 6\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 400\text{ V}$		-	192	-	ns
Reverse Recovery Charge	Q_{rr}			-	2.4	-	μC
Reverse Recovery Current	I_{RRM}			-	11	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

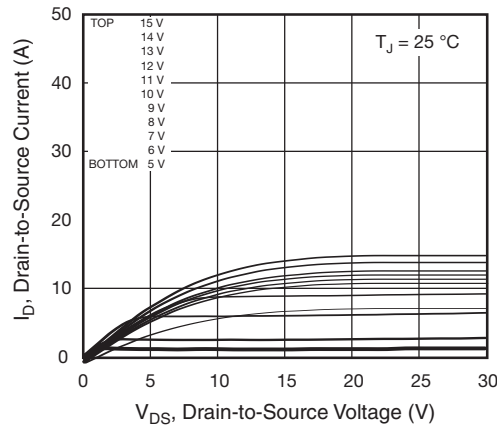


Fig. 1 - Typical Output Characteristics

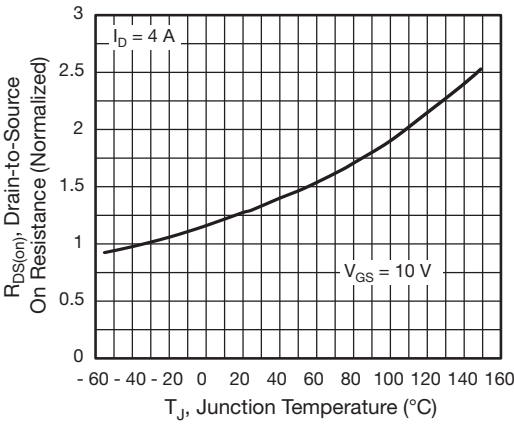


Fig. 4 - Normalized On-Resistance vs. Temperature

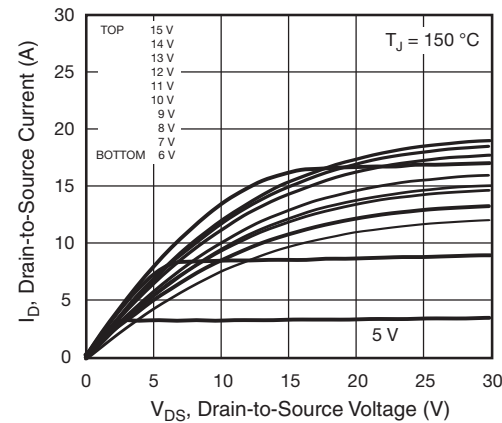


Fig. 2 - Typical Output Characteristics

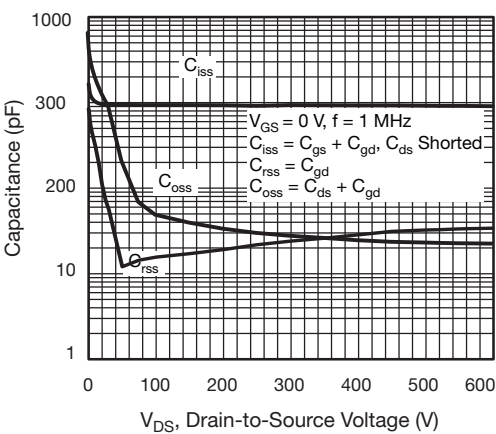


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

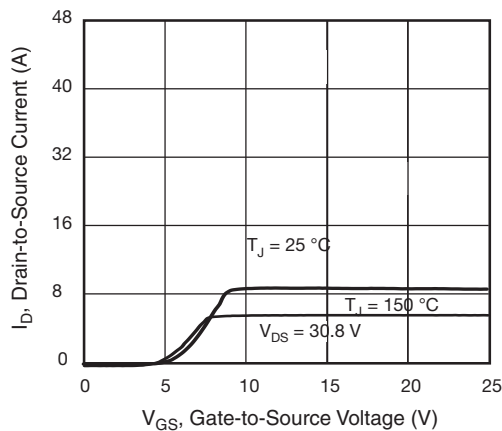


Fig. 3 - Typical Transfer Characteristics

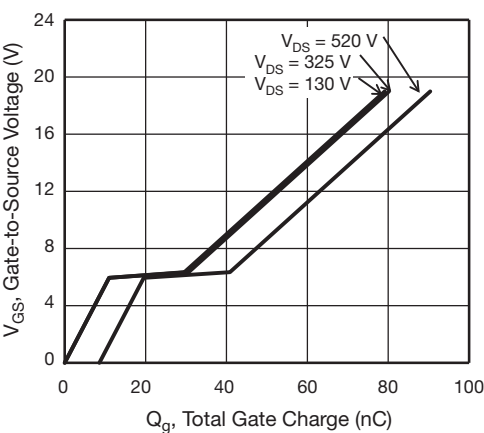


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

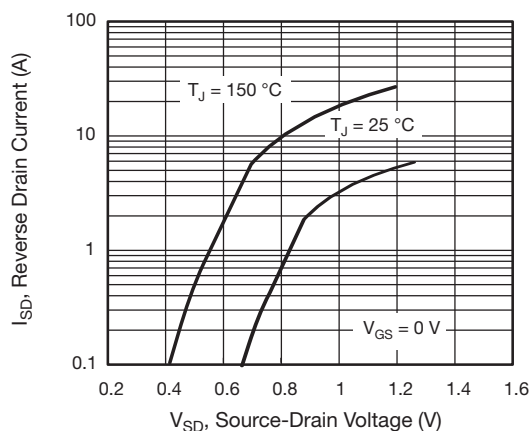


Fig. 7 - Typical Source-Drain Diode Forward Voltage

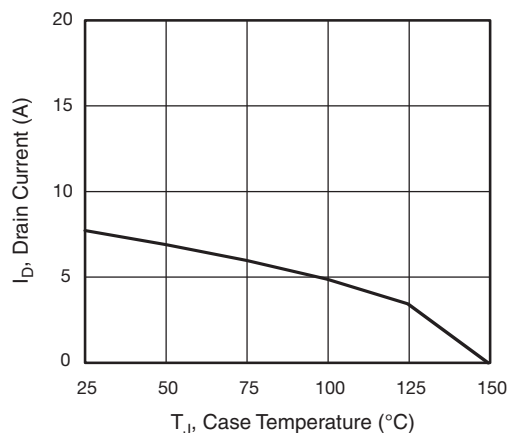


Fig. 9 - Maximum Drain Current vs. Case Temperature

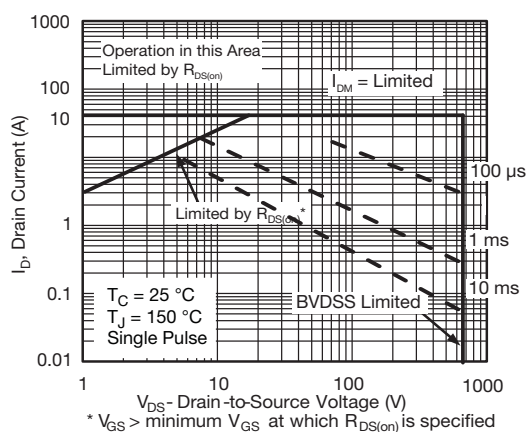


Fig. 8 - Maximum Safe Operating Area

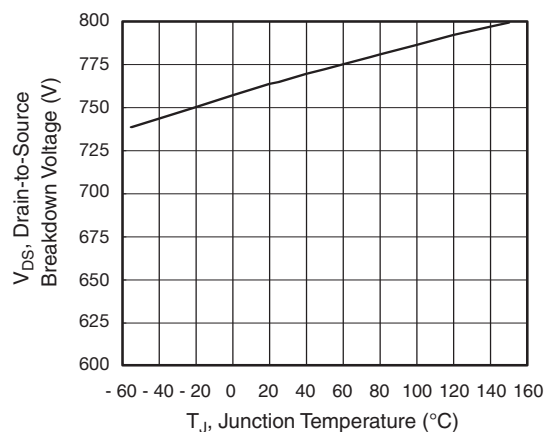


Fig. 10 - Temperature vs. Drain-to-Source Voltage

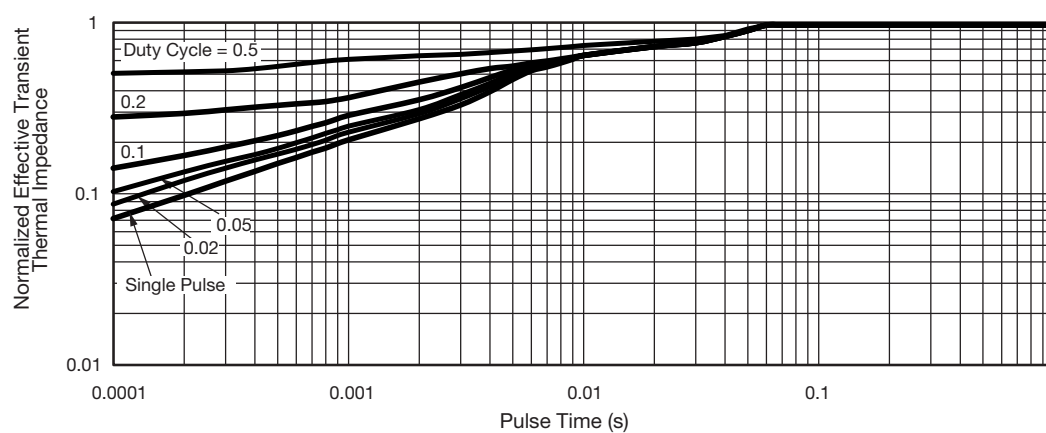


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

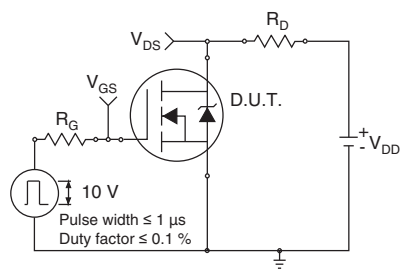


Fig. 12 - Switching Time Test Circuit

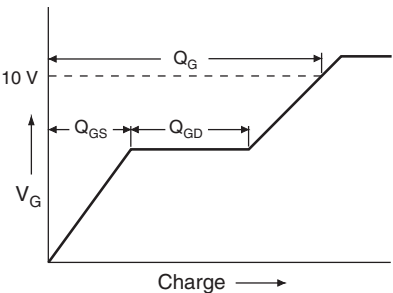


Fig. 16 - Basic Gate Charge Waveform

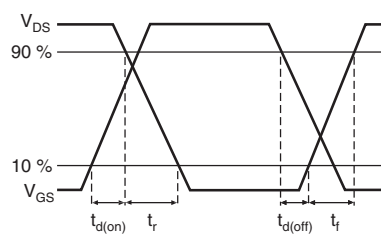


Fig. 13 - Switching Time Waveforms

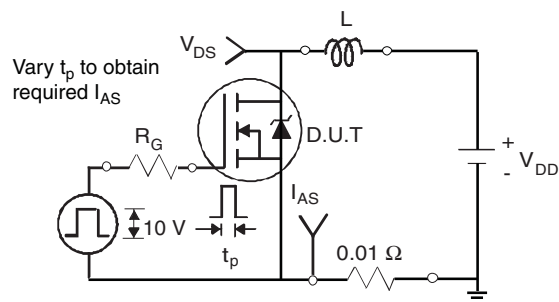


Fig. 14 - Unclamped Inductive Test Circuit

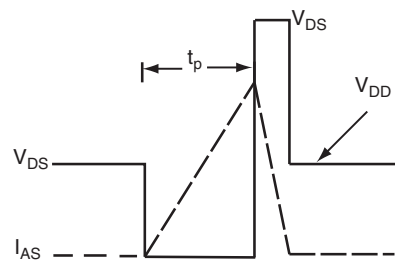


Fig. 15 - Unclamped Inductive Waveforms

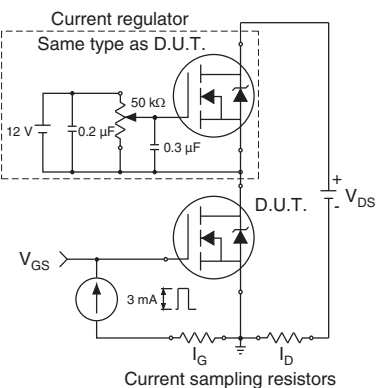
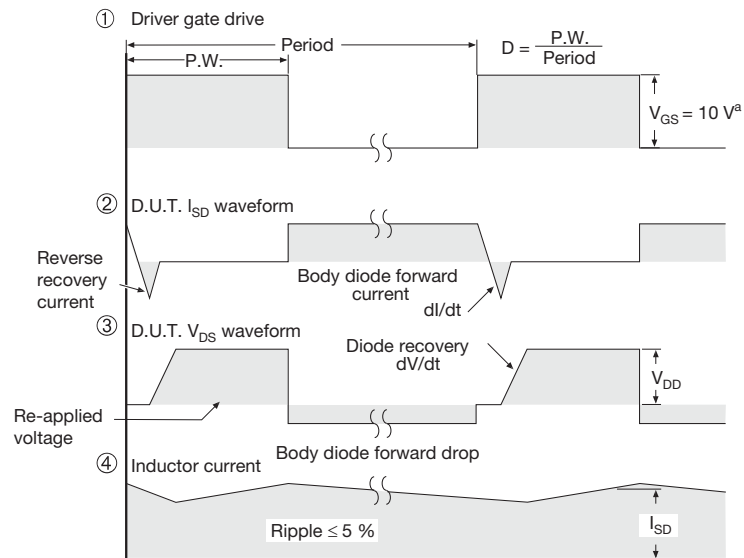
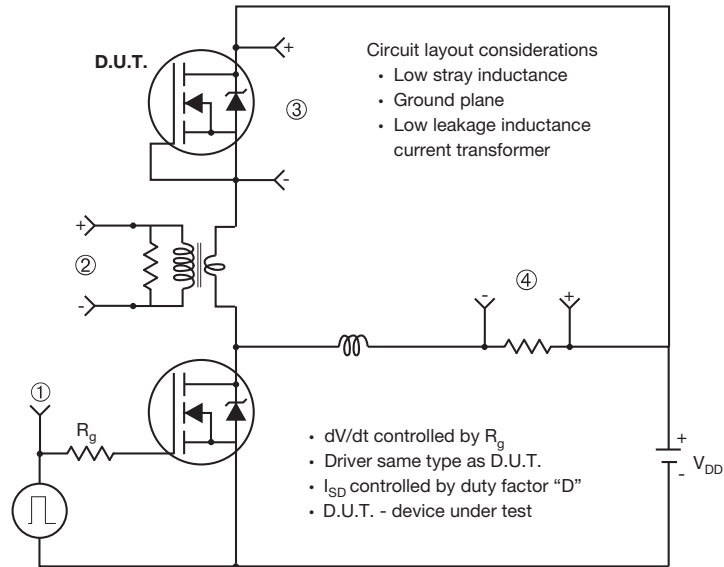


Fig. 17 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 18 - For N-Channel

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